

ABSTRACT

COMPOSITION FOR ADVANCED NODE FRONT- AND BACK-END OF LINE CHEMICAL MECHANICAL POLISHING

The present disclosure is directed to a highly dilutable chemical mechanical polishing concentrate comprising an abrasive, an acid, a stabilizer, and water with a point-of-use pH ranging from 2.2 - 3.5 for planarizing current and next generation semiconductor integrated circuit FEOL/BEOL substrates.

Fig 4